



JIANGSU CHANGJIANG ELECTRONICS TECHNOLOGY CO., LTD

TO-92MOD Plastic-Encapsulate Transistors

2SC2235 TRANSISTOR (NPN)

FEATURES

Complementary to 2SA965

MAXIMUM RATINGS ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

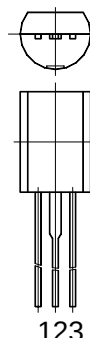
Symbol	Parameter	Value	Units
V_{CBO}	Collector-Base Voltage	120	V
V_{CEO}	Collector-Emitter Voltage	120	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current -Continuous	0.8	A
P_C	Collector Power Dissipation	0.9	W
T_J	Junction Temperature	150	$^{\circ}\text{C}$
T_{stg}	Storage Temperature	-55to+150	$^{\circ}\text{C}$

TO-92MOD

1. EMITTER

2. COLLECTER

3. BASE



ELECTRICAL CHARACTERISTICS ($T_{amb}=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Test conditions	MIN	TYP	MAX	UNIT
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1\text{mA}, I_E=0$	120			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	120			V
Emitter-Base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\text{mA}, I_C=0$	5			V
Collector cut-off current	I_{CBO}	$V_{CB}=120\text{V}, I_E=0$			0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=5\text{V}, I_C=0$			0.1	μA
DC current gain	h_{FE}	$V_{CE}=5\text{V}, I_C=100\text{mA}$	80		240	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=500\text{mA}, I_B=50\text{mA}$			1.0	V
Base-emitter voltage	V_{BE}	$I_C=500\text{mA}, V_{CE}=5\text{V}$			1.0	V
Transition frequency	f_T	$V_{CE}=5\text{V}, I_C=100\text{mA}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CE}=10\text{V}, I_E=0$ $f=1\text{MHz}$			30	pF

CLASSIFICATION OF h_{FE}

Rank	O	Y
Range	80-160	120-240

Typical Characteristics

2SC2235

